# N-Channel 600-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

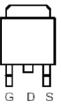
## **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vps (V)	$r_{DS(on)}(m\Omega)$	ID (A)		
600	360 @ V <sub>GS</sub> = 10V	.30 <sup>a</sup>		
600	375 @ V <sub>GS</sub> = 6.5V	30		







Top View

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			600	V		
Gate-Source Voltage	$V_{GS}$	±20	v			
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	30	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	120	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>	T <sub>C</sub> =25°C	ا <sub>s</sub>	30	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	300	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient °	R <sub>θJA</sub>	62.5	°C/W
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	0.5	C/W

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

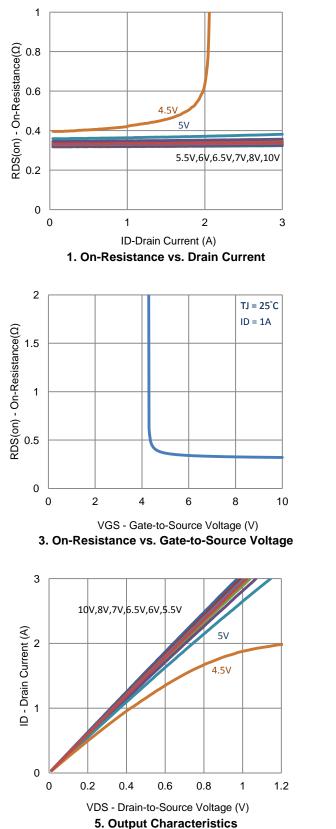
## **Electrical Characteristics**

Parameter	Symbol Test Conditions			Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA		
	I <sub>DSS</sub>	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	37.5			А		
Drain Course On Desistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$			360	mΩ		
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, \text{ I}_{D} = 8 \text{ A}$			375	11122		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 50 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		12		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 15 A, V <sub>GS</sub> = 0 V		0.94		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	Qg	$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 6.5 \text{ V},$ $I_{D} = 1 \text{ A}$		12		nC		
Gate-Source Charge	$Q_gs$			3.1				
Gate-Drain Charge	$Q_{gd}$			5.9				
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 100 \text{ V}, \text{ R}_{1} = 100 \Omega,$		11		ns		
Rise Time	t <sub>r</sub>	$V_{DS} = 100 V, K_L - 100 \Omega,$ $I_D = 1 A,$		11				
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		93				
Fall Time	t <sub>f</sub>	VGEN - 10 V, T(GEN - 0 22		44				
Input Capacitance	C <sub>iss</sub>			706				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50, V_{GS} = 0 V, f = 1 Mhz$		168		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			10				

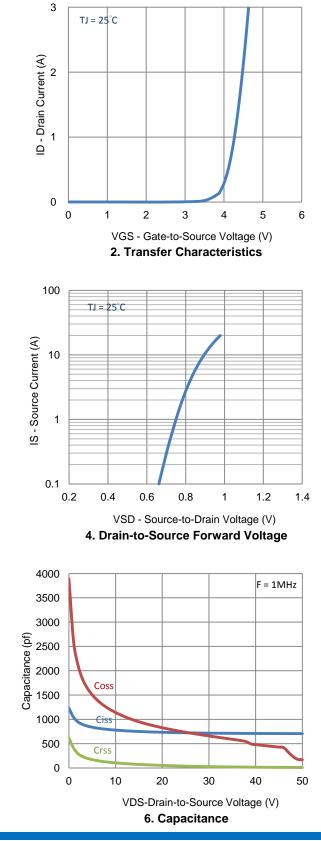
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

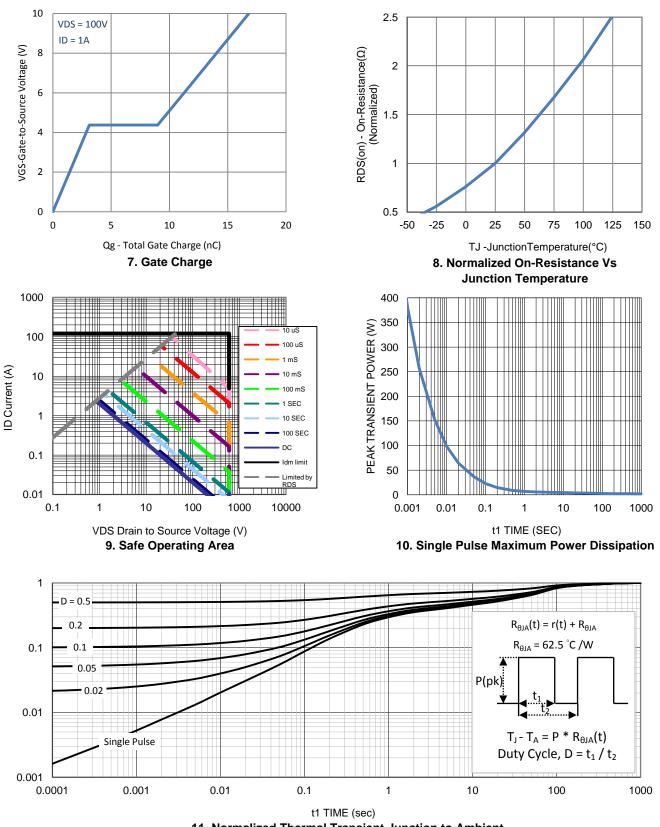
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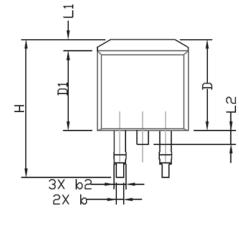
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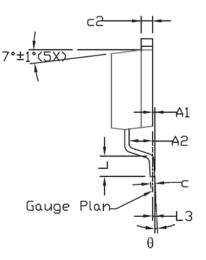


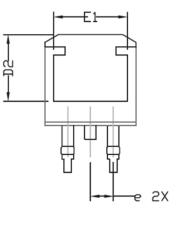
### **Typical Electrical Characteristics**

**11. Normalized Thermal Transient Junction to Ambient** 

# Package Information







	DIMENSIONAL REQMIS			INCHES REQMTS			
SYMBOL	MIN	NDM	MAX	MIN	NLM	MAX	
A	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0.105	
b	0.69	0.813	0.94	0.027	0.032	0.037	
b2	1.17	1,27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0,60	0.019	0.020	0.024	
c2	1,17	1.27	1.37	0.046	0.050	0.054	
D	9,80	10.05	10.30	0.386	0,396	0.406	
D1	8,64	8,78	9,65	0.340	0.346	0.380	
D5	7.12	7.37	7,62	0.280	0,290	0.300	
E	9,70	10.15	10.54	0,382	0.400	0.415	
E1	8,00	8,20	8,40	0.315	0,323	0.331	
e	2.	54 BSC		0.100 BSC			
H	14.99	15.24	15,49	0.590	0.600	0.610	
L	1.78	2.29	2,79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0.060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0°		8*	0*		8*	